

At page 10, lines 14-23, the paragraph should read:

B2
Figure 5 is an illustration of a computer system that can use and be used with embodiments of the present invention. As will be appreciated by those skilled in the art, the computer system would include ROM 514, mass memory 516, peripheral devices 518, and I/O devices 520 in communication with a microprocessor 522 via a data bus 524 or another suitable data communication path. The mass memory 516 can include silicon-containing barrier layers in, for example, transistor structures or charge storage structures. The mass memory 516 may further include a substrate, a drain, a source rail, and an oxide layer. Generally, the drain and source rail are formed in the substrate. The oxide layer is typically deposited over the substrate and stretches from the drain to the source rail. The silicon-containing barrier is generally deposited over the first oxide layer. These devices can be fabricated according with the various embodiments of the present invention.

The Abstract on page 23 should read:

ABSTRACT OF THE DISCLOSURE

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Systems and devices are disclosed utilizing a silicon-containing barrier layer. A semiconductor device is disclosed. The semiconductor device includes a substrate, a gate oxide, a silicon-containing barrier layer and a gate electrode. The gate oxide is formed over the substrate. The silicon-containing barrier layer is formed over the gate oxide by causing silicon atoms of a precursor layer react with a reactive agent. The gate electrode is formed over the silicon-containing barrier layer. Other embodiments utilizing a barrier layer are disclosed.

In the Claims

30. (Amended) A capacitor device comprising:

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- a first electrode formed over a substrate;
 - a primarily nitride silicon-containing barrier layer on said first electrode, said barrier layer comprising a silicon-containing material from a precursor layer, previously deposited over at least a portion of said first electrode, that has been reacted with a nitridizing agent;
 - a dielectric layer formed over the primarily nitride silicon-containing barrier layer; and
 - a second electrode formed over the dielectric layer.